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5/05—Rev. 0 to Rev. A

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4/94–Revision 0: Initial Version

SPECIFICATIONS

DUAL SUPPLY[1]

V_{DD} = +15 V ± 10%, V_{SS} = −15 V ± 10%, V_L = +5 V ± 10% (ADG444), GND = 0 V, unless otherwise noted.

Table 1.

Parameter	B Version +25°C	B Version −40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		V_{SS} to V_{DD}	V	
R_{ON}	40		Ω typ	V_D = ±8.5 V, I_S = −10 mA
	70	85	Ω max	V_{DD} = +13.5 V, V_{SS} = −13.5 V
ΔR_{ON}		4	Ω typ	−8.5 V ≤ V_D ≤ +8.5 V
		9	Ω max	
R_{ON} Match		1	Ω typ	V_D = 0 V, I_S = −10 mA
		3	Ω max	
LEAKAGE CURRENTS				V_{DD} = +16.5 V, V_{SS} = −16.5 V
Source OFF Leakage I_S (OFF)	±0.01		nA typ	V_D = ±15.5 V, V_S = ∓15.5 V
	±0.5	±3	nA max	See Figure 15
Drain OFF Leakage I_D (OFF)	±0.01		nA typ	V_D = ±15.5 V, V_S = ∓15.5 V
	±0.5	±3	nA max	See Figure 15
Channel ON Leakage I_D, I_S (ON)	±0.08		nA typ	V_S = V_D = ±15.5 V
	±0.5	±3	nA max	See Figure 16
DIGITAL INPUTS				
Input High Voltage, V_{INH}		2.4	V min	
Input Low Voltage, V_{INL}		0.8	V max	
Input Current				
I_{INL} or I_{INH}		±0.00001	μA typ	V_{IN} = V_{INL} or V_{INH}
		±0.5	μA max	
DYNAMIC CHARACTERISTICS[2]				
t_{ON}	85		ns typ	R_L = 1 kΩ, C_L = 35 pF;
	110	170	ns max	V_S = ±10 V; see Figure 17
t_{OFF}	45		ns typ	R_L = 1 kΩ, C_L = 35 pF;
	60	80	ns max	V_S = ±10 V; see Figure 17
t_{OPEN}	30		ns typ	R_L = 1 kΩ, C_L = 35 pF;
Charge Injection	1		pC typ	V_S = 0 V, R_S = 0 Ω, C_L = 1 nF;
	6		pC max	V_{DD} = +15 V, V_{SS} = −15 V; see Figure 18
OFF Isolation	60		dB typ	R_L = 50 Ω, C_L = 5 pF; f = 1 MHz; see Figure 19
Channel-to-Channel Crosstalk	100		dB typ	R_L = 50 Ω, C_L = 5 pF; f= 1 MHz; see Figure 20
C_S (OFF)	4		pF typ	f = 1 MHz
C_D (OFF)	4		pF typ	f = 1 MHz
C_D, C_S (ON)	16		pF typ	f = 1 MHz
POWER REQUIREMENTS				V_{DD} = +16.5 V, V_{SS} = −16.5 V
I_{DD}				Digital Inputs = 0 V or 5 V
ADG441/ADG442		80	μA max	
ADG444	0.001		μA typ	
	1	2.5	μA max	
I_{SS}	0.0001		μA typ	
	1	2.5	μA max	
I_L (ADG444 Only)	0.001		μA typ	V_L = 5.5 V
	1	2.5	μA max	

[1] Temperature range is: B Version: −40°C to +85°C.
[2] Guaranteed by design, not subject to production test.

SINGLE SUPPLY[1]

V_{DD} = +12 V ± 10%, V_{SS} = 0 V, V_L = +5 V ± 10% (ADG444), GND = 0 V, unless otherwise noted.

Table 2.

Parameter	B Version +25°C	B Version −40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		0 to V_{DD}	V	
R_{ON}	70		Ω typ	V_D = +3 V, +8 V, I_S = −5 mA
	110	130	Ω max	V_{DD} = 10.8 V
ΔR_{ON}		4	Ω typ	3 V ≤ V_D ≤ 8 V
		9	Ω max	
R_{ON} Match		1	Ω typ	V_D = +6 V, I_S = −5 mA
		3	Ω max	
LEAKAGE CURRENT				V_{DD} = 13.2 V
Source OFF Leakage I_S (OFF)	±0.01		nA typ	V_D = 12.2 V/1 V, V_S = 1 V/12.2 V
	±0.5	±3	nA max	See Figure 15
Drain OFF Leakage I_D (OFF)	±0.01		nA typ	V_D = 12.2 V/1 V, V_S = 1 V/12.2 V
	±0.5	±3	nA max	See Figure 15
Channel ON Leakage I_D, I_S (ON)	±0.08		nA typ	V_S = V_D = 12.2 V/1 V
	±0.5	±3	nA max	Figure 16
DIGITAL INPUTS				
Input High Voltage, V_{INH}		2.4	V min	
Input Low Voltage, V_{INL}		0.8	V max	
Input Current				
I_{INL} or I_{INH}		±0.00001	μA typ	V_{IN} = V_{INL} or V_{INH}
		±0.5	μA max	
DYNAMIC CHARACTERISTICS[2]				
t_{ON}	105		ns typ	R_L = 1 kΩ, C_L = 35 pF
	150	220	ns max	V_S = 8 V; Figure 17
t_{OFF}	40		ns typ	R_L = 1 kΩ, C_L = 35 pF
	60	100	ns max	V_S = 8 V; Figure 17
t_{OPEN}	50		ns typ	R_L = 1 kΩ, C_L = 35 pF
Charge Injection	2		pC typ	V_S = 6 V, R_S = 0 Ω, C_L = 1 nF
	6		pC max	V_{DD} = 12 V, V_{SS} = 0 V; see Figure 18
OFF Isolation	60		dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 19
Channel-to-Channel Crosstalk	100		dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 20
C_S (OFF)	7		pF typ	f = 1 MHz
C_D (OFF)	10		pF typ	f = 1 MHz
C_D, C_S (ON)	16		pF typ	f = 1 MHz
POWER REQUIREMENTS				V_{DD} = 13.2 V
I_{DD}				Digital Inputs = 0 V or 5 V
ADG441/ADG442		80	μA max	
ADG444	0.001		μA typ	
	1	2.5	μA max	
I_L (ADG444 Only)	0.001		μA typ	V_L = 5.5 V
	1	2.5	μA max	

[1] Temperature range is: B Version: −40°C to +85°C.
[2] Guaranteed by design, not subject to production test.

ABSOLUTE MAXIMUM RATINGS

T_A = 25°C unless otherwise noted.

Table 3.

Parameter	Rating
V_{DD} to V_{SS}	44 V
V_{DD} to GND	−0.3 V to +25 V
V_{SS} to GND	+0.3 V to −25 V
V_L to GND	−0.3 V to V_{DD} + 0.3 V
Analog, Digital Inputs	V_{SS} − 2 V to V_{DD} + 2 V or 30 mA, Whichever Occurs First
Continuous Current, S or D	30 mA
Peak Current, S or D (Pulsed at 1 ms, 10% Duty Cycle Max)	100 mA
Operating Temperature Range	
Industrial (B Version)	−40°C to +85°C
Storage Temperature Range	−65°C to +150°C
Junction Temperature	150°C
Lead Temperature, Soldering (10 sec)	300°C
Plastic Package, Power Dissipation	470 mW
θ_{JA}, Thermal Impedance	177°C/W
Lead Temperature, Soldering (10 sec)	260°C
SOIC Package, Power Dissipation	600 mW
θ_{JA}, Thermal Impedance	77°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec)	215°C
Infrared (15 sec)	220°C

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 4. Truth Table

ADG441/ADG444 IN	ADG442 IN	Switch Condition
0	1	ON
1	0	OFF

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

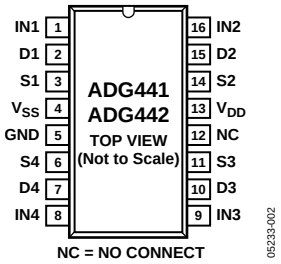


Figure 2. ADG441/ADG442 (DIP/SOIC)

Table 5. ADG441/ADG442 Pin Function Descriptions

Pin No.	Mnemonic	Description
1, 8, 9, 16	IN1 to IN4	Logic Control Input.
2, 7, 10, 15	D1 to D4	Drain Terminal. May be an input or output.
3, 6, 11, 14	S1 to S4	Source Terminal. May be an input or output.
4	V_{SS}	Most Negative Power Supply Potential in Dual Supplies. In single-supply applications, it may be connected to ground.
5	GND	Ground (0 V) Reference.
12	NC	No Connect.
13	V_{DD}	Most Positive Power Supply Potential.

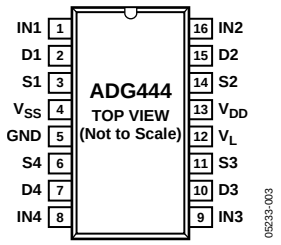


Figure 3. ADG444 (DIP/SOIC)

Table 6. ADG444 Pin Function Descriptions

Pin No.	Mnemonic	Description
1, 8, 9, 16	IN1 to IN4	Logic Control Input.
2, 7, 10, 15	D1 to D4	Drain Terminal. May be an input or output.
3, 6, 11, 14	S1 to S4	Source Terminal. May be an input or output.
4	V_{SS}	Most Negative Power Supply Potential in Dual Supplies. In single-supply applications, it may be connected to ground.
5	GND	Ground (0 V) Reference.
12	V_L	Logic Power Supply (5 V).
13	V_{DD}	Most Positive Power Supply Potential.

TYPICAL PERFORMANCE CHARACTERISTICS

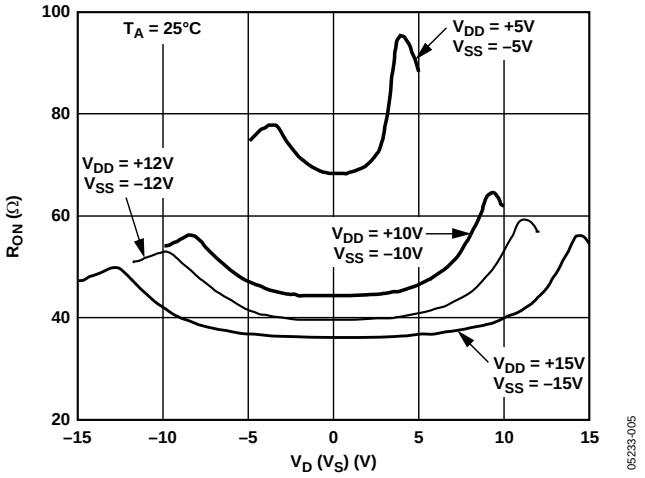


Figure 4. R_{ON} as a Function of V_D (V_S): Dual Supply

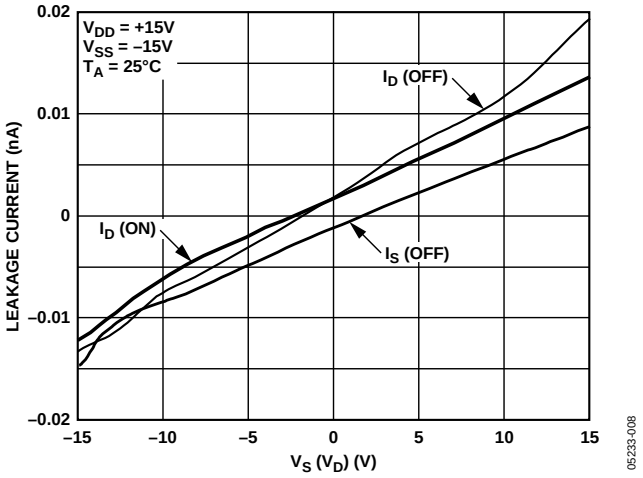


Figure 7. Leakage Currents as a Function of V_S (V_D)

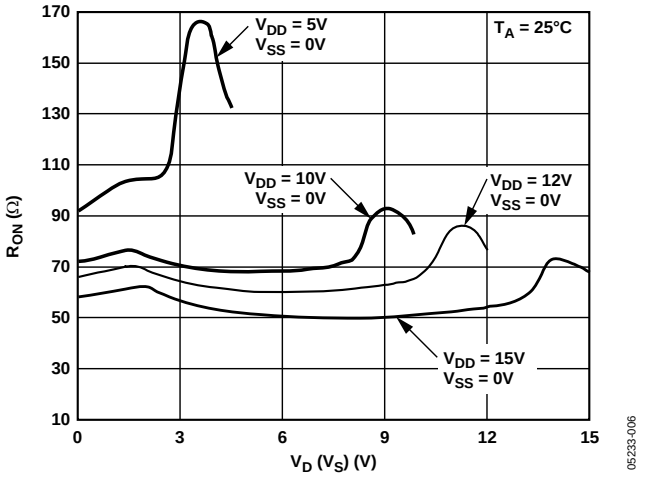


Figure 5. R_{ON} as a Function of V_D (V_S): Single Supply

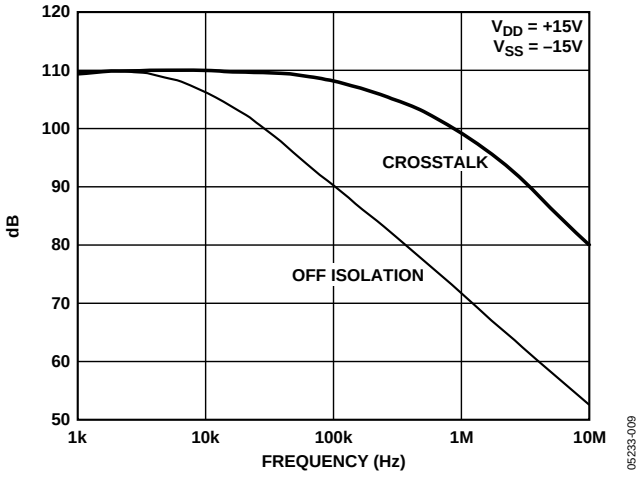


Figure 8. Crosstalk and Off Isolation vs. Frequency

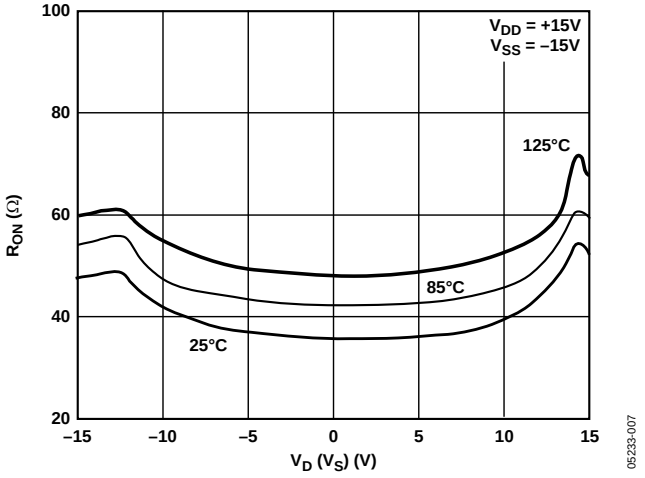


Figure 6. R_{ON} as a Function of V_D (V_S) for Different Temperatures

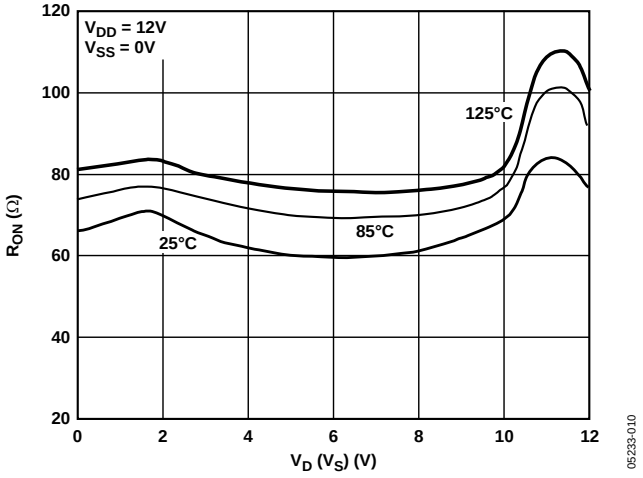


Figure 9. R_{ON} as a Function of V_D (V_S) for Different Temperatures

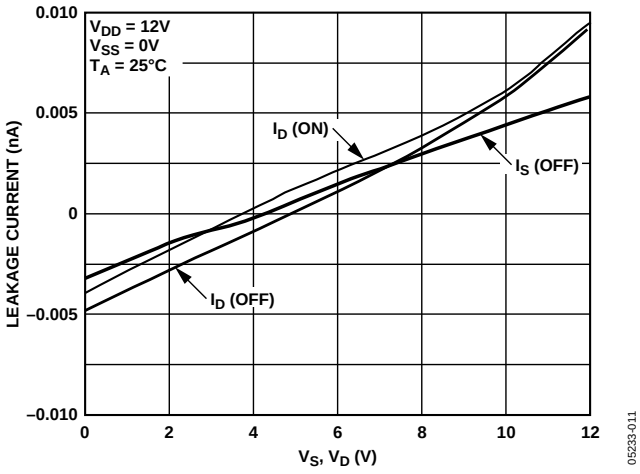


Figure 10. Leakage Currents as a Function of V_S (V_D)

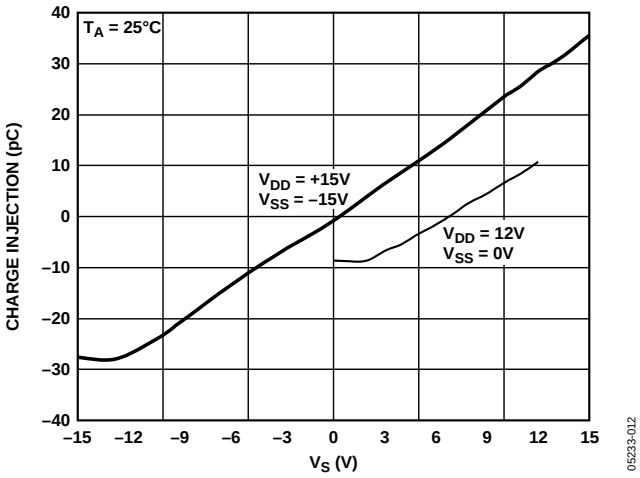


Figure 11. Charge Injection vs. Source Voltage

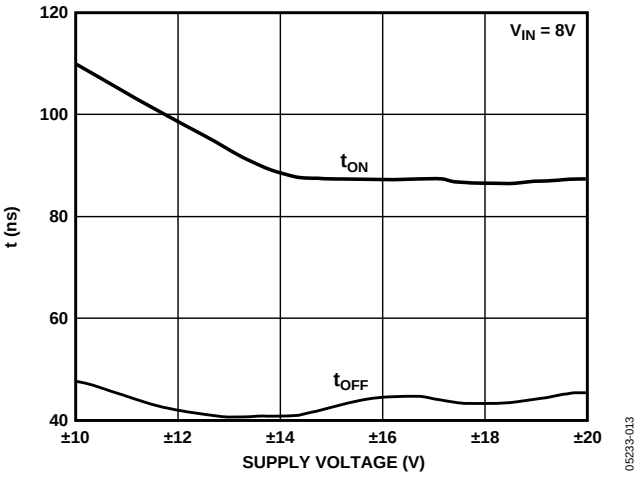


Figure 12. Switching Time vs. Bipolar Supply

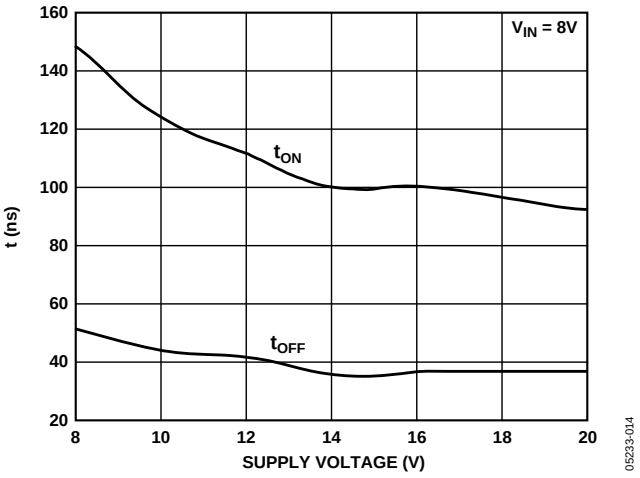


Figure 13. Switching Time vs. Single Supply

TEST CIRCUITS

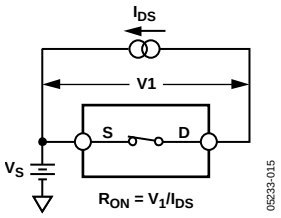


Figure 14. On Resistance

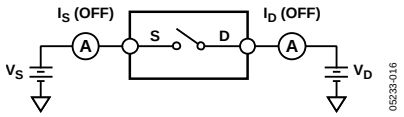


Figure 15. Off Leakage

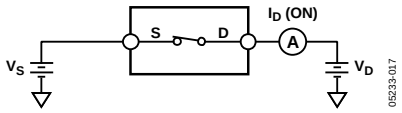


Figure 16. On Leakage

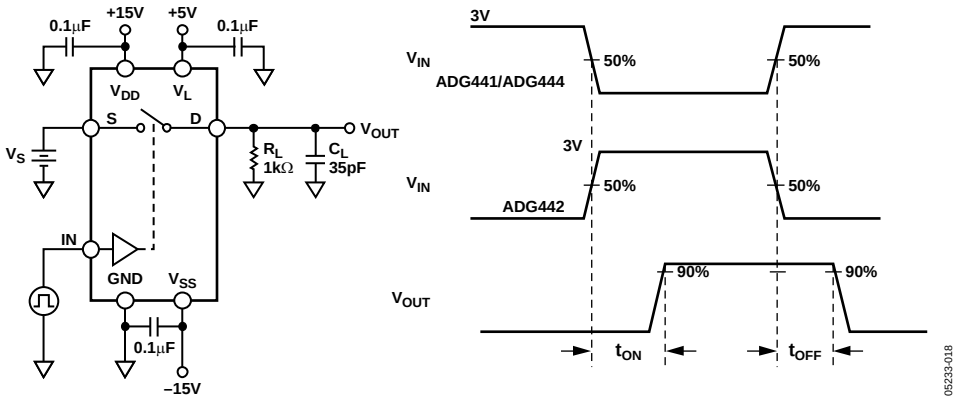


Figure 17. Switching Times

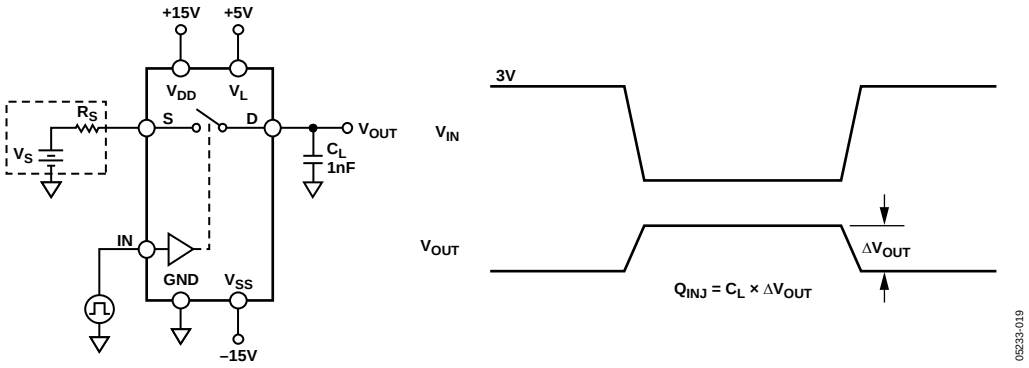


Figure 18. Charge Injection

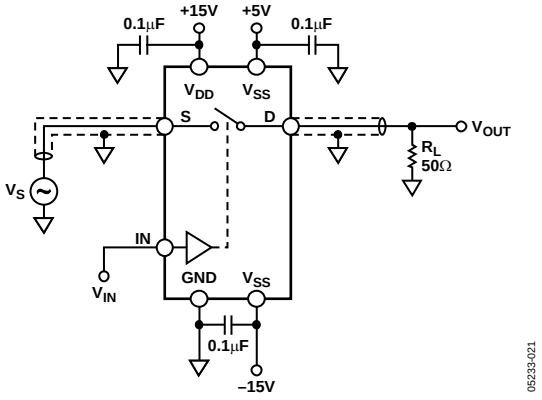


Figure 19. Off Isolation

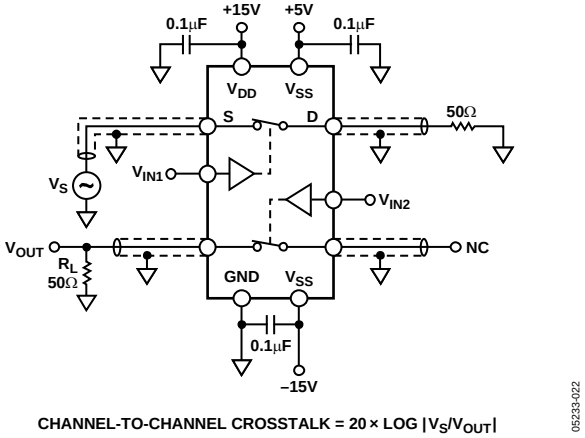


Figure 20. Channel-to-Channel Crosstalk

TERMINOLOGY

R_{ON}
Ohmic resistance between D and S.

R_{ON} Match
Difference between the R_{ON} of any two channels.

I_S (OFF)
Source leakage current with the switch OFF.

I_D (OFF)
Drain leakage current with the switch OFF.

I_D, I_S (ON)
Channel leakage current with the switch ON.

V_D (V_S)
Analog voltage on Terminals D, S.

C_S (OFF)
OFF switch source capacitance.

C_D (OFF)
OFF switch drain capacitance.

C_D, C_S (ON)
ON switch capacitance.

t_{ON}
Delay between applying the digital control input and the output switching on.

t_{OFF}
Delay between applying the digital control input and the output switching off.

t_{OPEN}
Break-before-make delay when switches are configured as a multiplexer.

Crosstalk
A measure of unwanted signal which is coupled through from one channel to another as a result of parasitic capacitance.

Off Isolation
A measure of unwanted signal coupling through an OFF switch.

Charge Injection
A measure of the glitch impulse transferred from the digital input to the analog output during switching.

TRENCH ISOLATION

In the ADG441A, ADG442A, and ADG444A, an insulating oxide layer (trench) is placed between the NMOS and the PMOS transistors of each CMOS switch. Parasitic junctions, which occur between the transistors in junction isolated switches, are eliminated, and the result is a completely latch-up proof switch.

In junction isolation, the N and P wells of the PMOS and NMOS transistors form a diode that is reverse-biased under normal operation. However, during overvoltage conditions, this diode becomes forward-biased. A silicon-controlled rectifier (SCR) type circuit is formed by the two transistors causing a significant amplification of the current which, in turn, leads to latch-up. With trench isolation, this diode is removed, and the result is a latch-up proof switch.

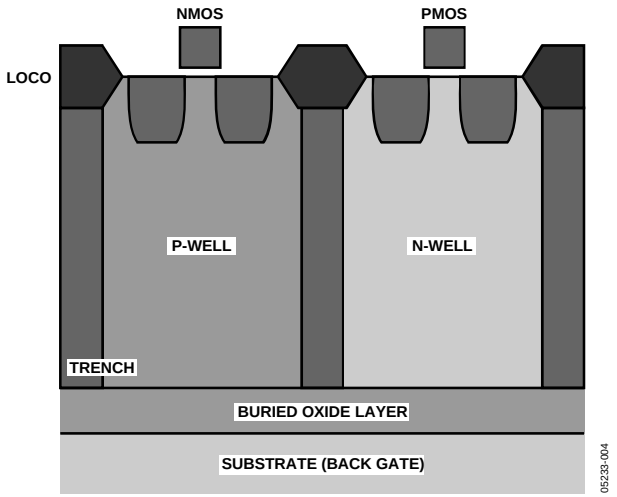
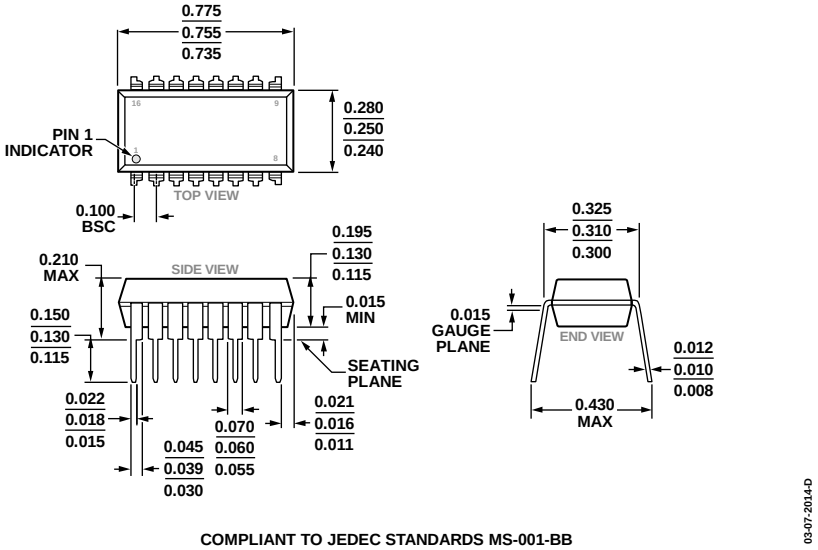


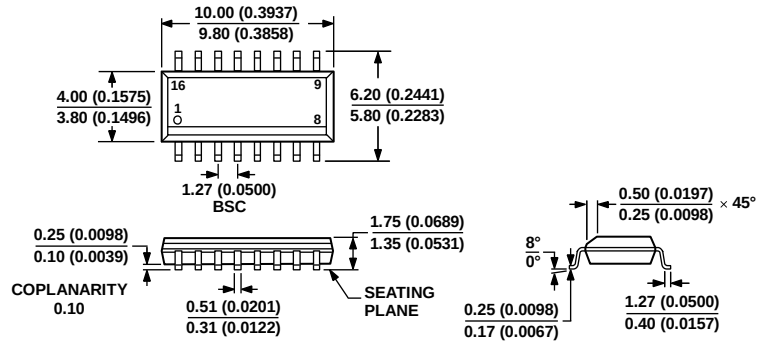
Figure 21. Trench Isolation

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MS-001-BB

Figure 22. 16-Lead Plastic Dual In-Line Package [PDIP]
Narrow Body
(N-16)
Dimensions shown in inches



COMPLIANT TO JEDEC STANDARDS MS-012-AC

CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 23. 16-Lead Standard Small Outline Package [SOIC_N]
(R-16)
Dimensions shown in millimeters and (inches)

ORDERING GUIDE

Model[1, 2]	Temperature Range	Package Description	Package Option
ADG441BNZ	−40°C to +85°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG441BR	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG441BR-REEL	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG441BRZ	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG441BRZ-REEL	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG441ABCHIPS		DIE	
ADG441ABR-REEL	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG441ABRZ-REEL	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG442BNZ	−40°C to +85°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG442BRZ	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG442BRZ-REEL	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG444BNZ	−40°C to +85°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG444BR	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG444BR-REEL	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG444BRZ	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG444BRZ-REEL	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16

[1] Z = RoHS Compliant Part.
[2] A = Trench isolated.

NOTES

NOTES